

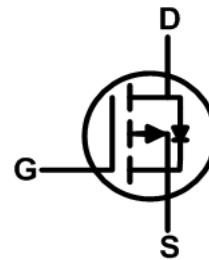


- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

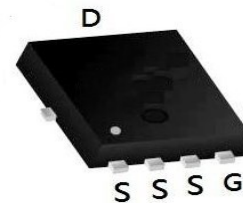
Description

The WLQ80P03F is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications .

The WLQ80P03F meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.



PDFN5060-8L Pin Configuration



Product Summary

BVDSS	R_{DS(on)}	I_D
-30V	6.3mΩ	-80A

Absolute Maximum Ratings

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current@-10V ¹	T _C =25°C	I _D	-80	A
	T _C =75°C		-42	
Pulsed Drain Current ²		I _{DM}	-175	A
Single Pulse Avalanche Energy ³		EAS	31	mJ
Avalanche Current		I _{AS}	-25	A
Total Power Dissipation ⁴	T _C =25°C	P _D	31.2	W
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to+150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ¹	R _{θJA}	43	°C/W
Thermal Resistance from Junction-to-Case ¹	R _{θJC}	4	°C/W



Electrical Characteristics T_c = 25°C, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V_{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30	-	-	V
Gate-body Leakage current	I_{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	V _{DS} = -24V, V _{GS} = 0V	-	-	-0.9	μA
	T _J =55°C		-	-	-5	
Gate-Threshold Voltage	V_{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-	-2.5	V
Drain-Source On-Resistance ²	R_{DS(on)}	V _{GS} = -10V, I _D = -12A	-	6.3	7.6	mΩ
		V _{GS} = -4.5V, I _D = -8A	-	11.5	14	
Forward Transconductance	g_{fs}	V _{DS} = -5V, I _D = -20A	-	28	-	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	V _{DS} = -15V, V _{GS} = 0V, f = 1MHz	-	4320	-	pF
Output Capacitance	C_{oss}		-	529	-	
Reverse Transfer Capacitance	C_{rss}		-	487	-	
Switching Characteristics						
Gate Resistance	R_g	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz	-	4.0	-	Ω
Total Gate Charge	Q_g	V _{GS} = -10V, V _{DS} = -15V, I _D = -15A	-	45	-	nC
Gate-Source Charge	Q_{gs}		-	8.5	-	
Gate-Drain Charge	Q_{gd}		-	12.8	-	
Turn-On Delay Time	t_{d(on)}	V _{GS} = -10V, V _{DD} = -15V, R _G = 2.5Ω, I _D = -15A	-	18.9	-	nS
Rise Time	t_r		-	15.7	-	
Turn-Off Delay Time	t_{d(off)}		-	64.8	-	
Fall Time	t_f		-	36.5	-	
Drain-Source Body Diode Characteristics						
Diode Forward Voltage ²	V_{SD}	I _S = -1A, V _{GS} = 0V	-	-	-1	V
Continuous Source Current ^{1,5}	I_S	V _G =V _D =0V, Force Current	-	-	-80	A

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}= -25V, V_{GS}= -10V, L= 0.1mH, I_{AS}= -25A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

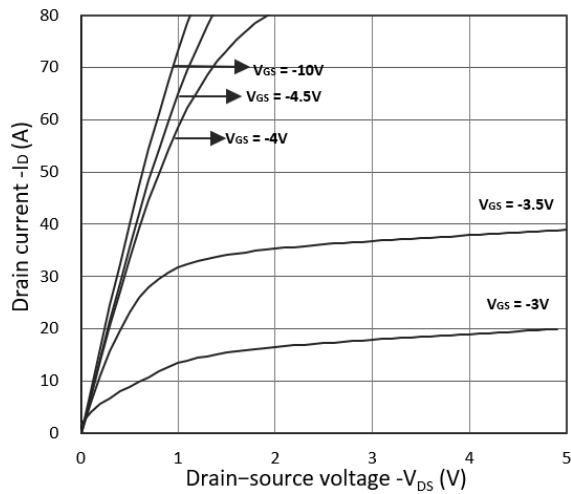


Figure 1. Output Characteristics

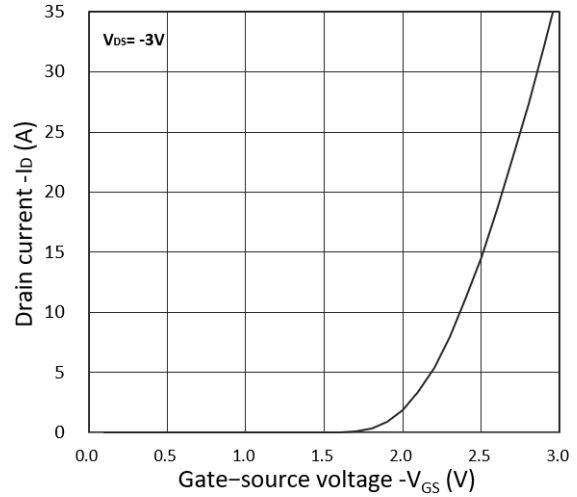


Figure 2. Transfer Characteristics

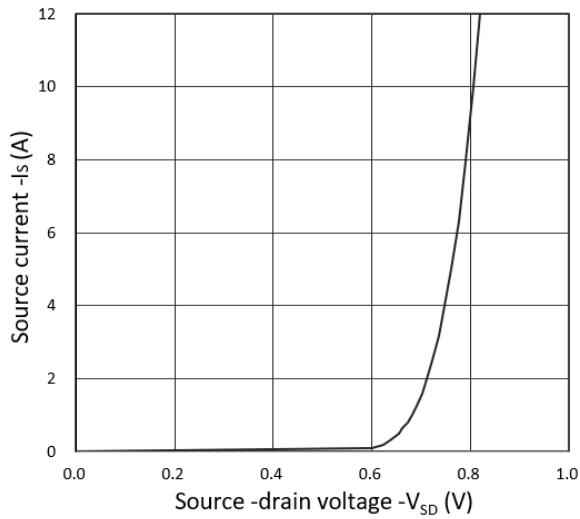


Figure 3. Forward Characteristics of Reverse

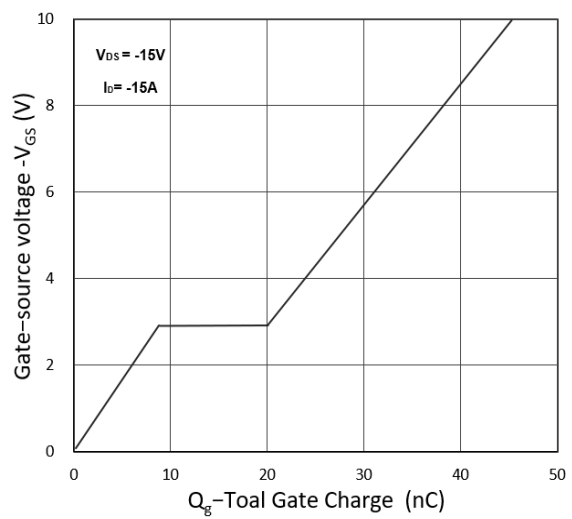


Figure 4. Gate Charge Characteristics

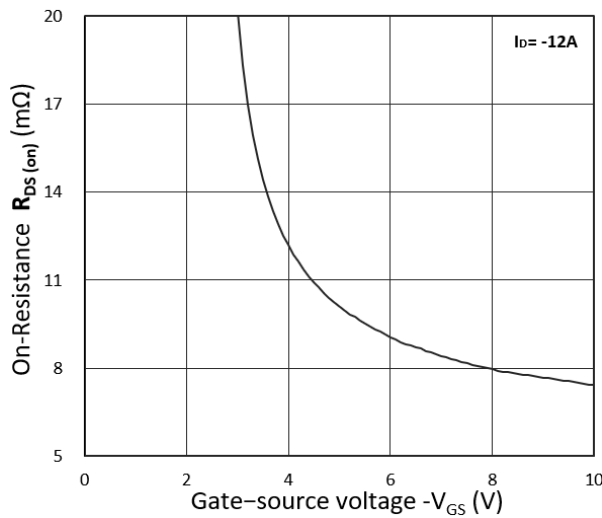


Figure 5. $R_{DS(on)}$ vs. V_{GS}

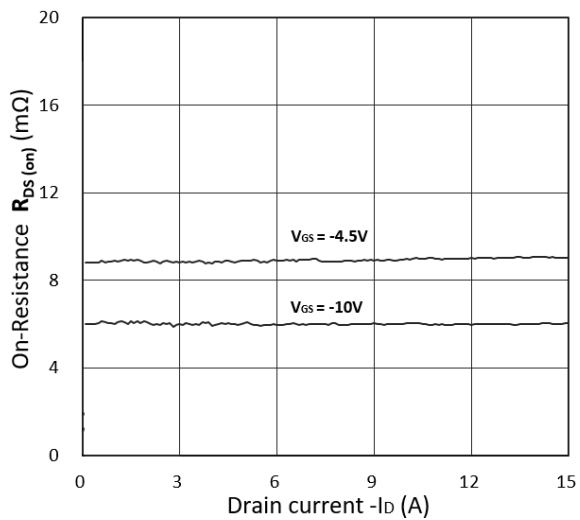


Figure 6. $R_{DS(on)}$ vs. I_D

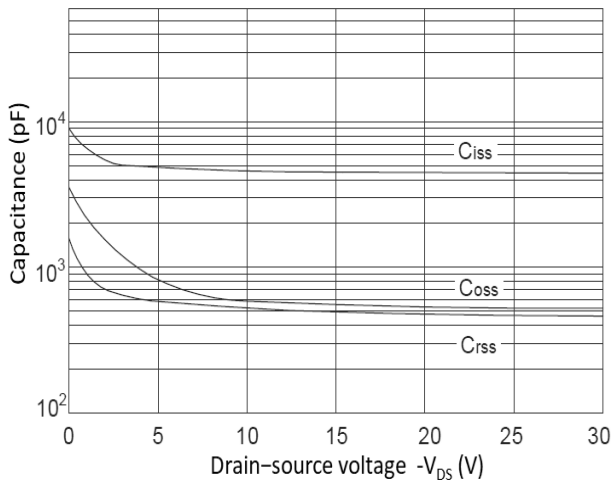


Figure 7. Capacitance Characteristics

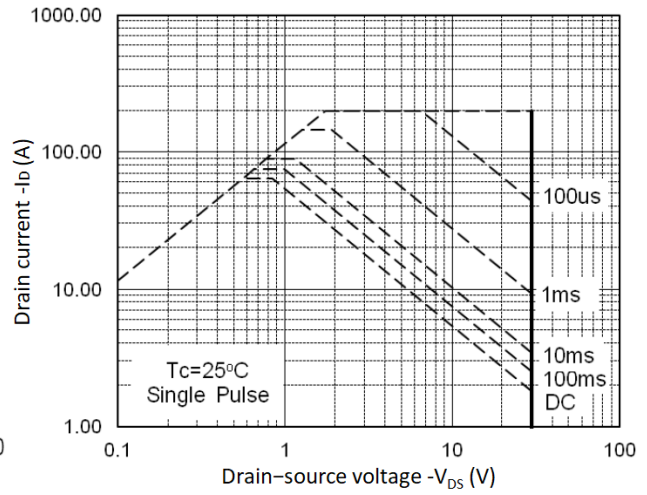


Figure 8. Safe Operating Area

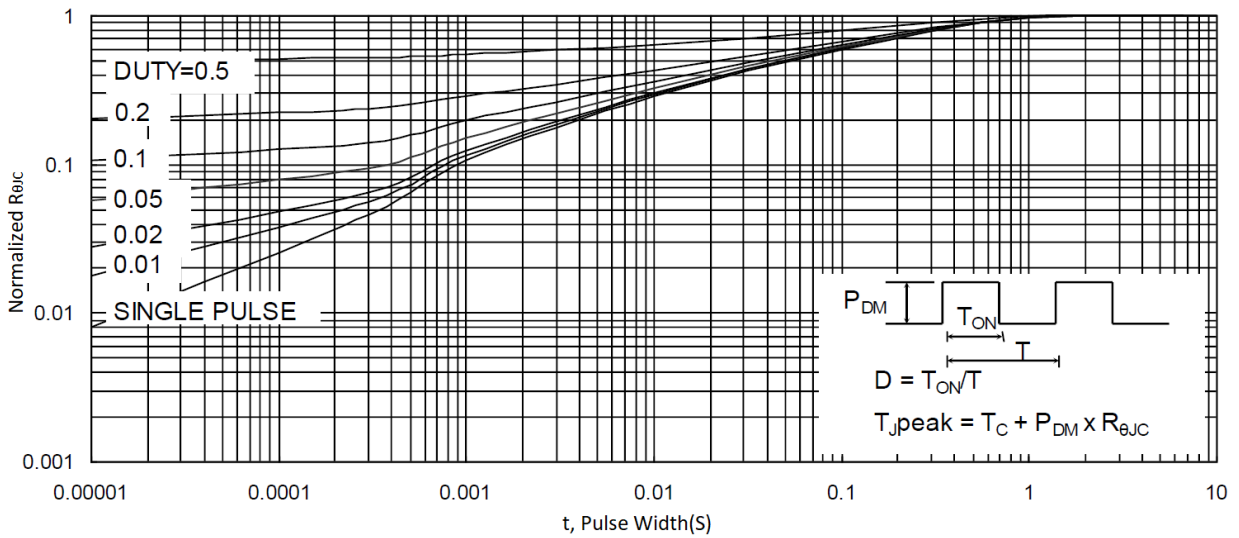


Figure 9. Normalized Maximum Transient Thermal Impedance

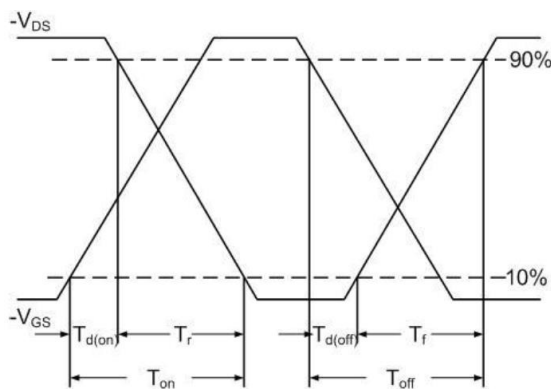


Figure 10. Switching Time Waveform

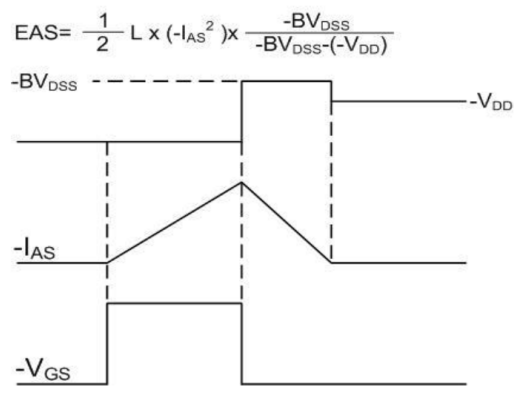
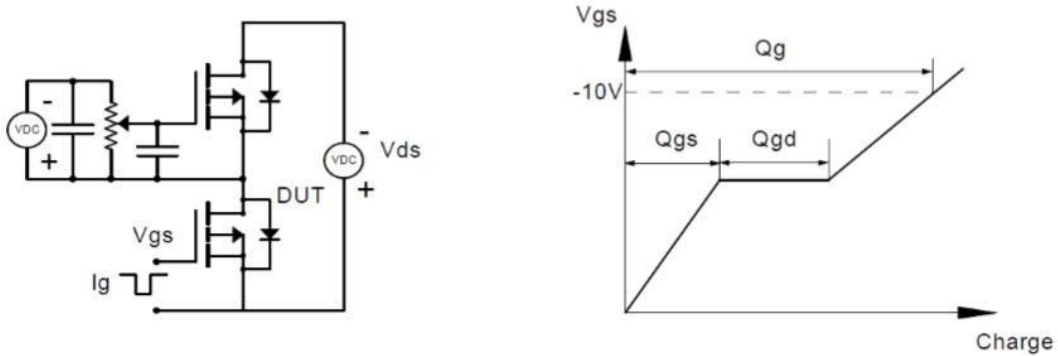


Figure 11. Unclamped Inductive Switching Waveform

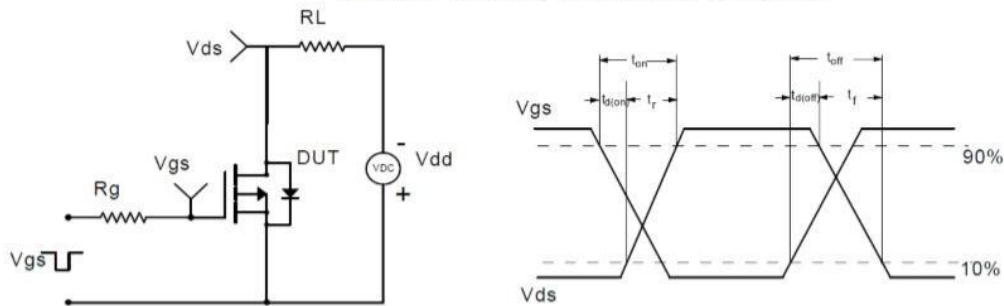


Test Circuit

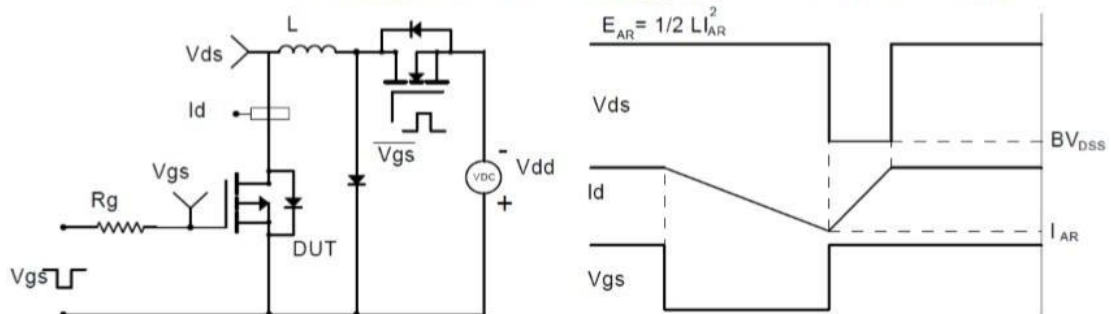
Gate Charge Test Circuit & Waveform



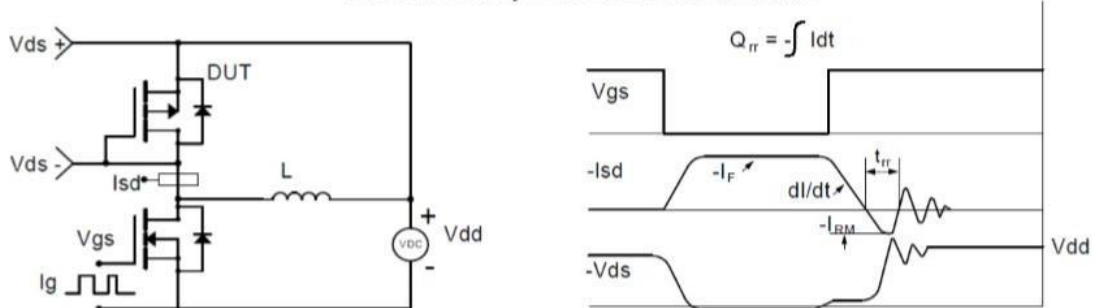
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

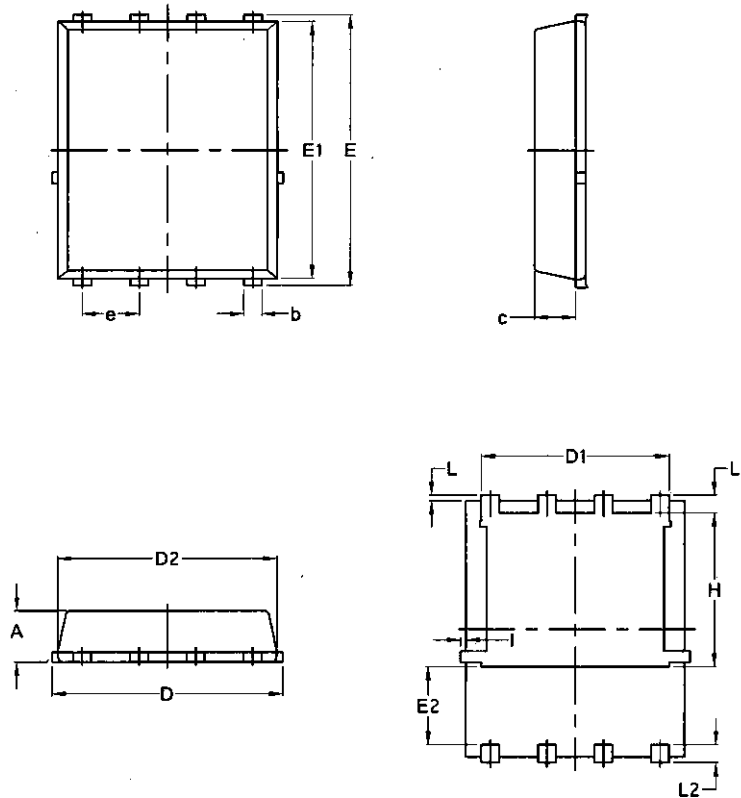


Diode Recovery Test Circuit & Waveforms





Package Mechanical Data-PDFN5060-8L-Single



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070



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